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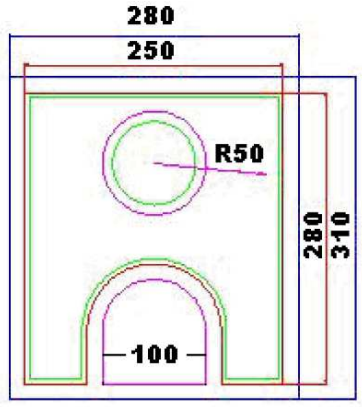
Data Sheet

LED Chip blue EOLC-470-34

Rev. 05, 2020

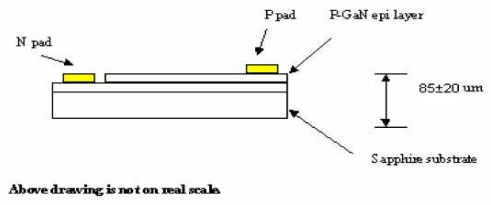
Radiation	Type	Electrodes
blue	GaN / sapphire	P + N up



All sizes in µm

Description

- Substrate: sapphire, epitaxial layer: GaN based material
- N bonding pad electrode: Au alloy
- P bonding pad electrode: Au alloy



Maximum Ratings

T_{amb}= 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward current (DC)		I_F			20	mA
Peak forward current	$t_p \leq$ 50 µs, t_p/T=½	I_{FM}			100	mA

Optical and Electrical Characteristics

T_{amb}= 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F=20 mA	V_F		3.3	3.5	V
Reverse current	V_R=5 V	I_R			1	µA
Luminous intensity*	I_F=20 mA	I_v	260	280	300	mcd
Dominant wavelength	I_F=20 mA	λ_p	467	470	473	nm
FWHM	I_F=20 mA	$\Delta\lambda_{0.5}$		30		nm

*Measured on bare chip on TO-18 header

Packing

Chips on adhesive film with wire-bond side top

Art. No. 112 109

RoHS COMPLIANT Pb-Free